

# **SOT-23 Plastic-Encapsulate MOSFETS**

#### 30V N-Channel MOSFET

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Typ	I <sub>D</sub> Max	
60V	105mΩ@10V	3A	
	125mΩ@4.5V		

High power and current handing capability

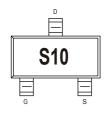
#### **DESCRIPTION**

The SI2310 uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltage as low as 2.5V. This device is suitable for use as a battery protection or in other switching application.

# **FEATURE APPLICATION**

- Lead free product is acquired
- Surface mount package

#### **MARKING**

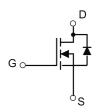


- **Battery Switch**
- DC/DC Converter

**SOT-23** 

1. GATE 2. SOURCE 3. DRAIN

## **Equivalent circuit**



#### **PACKAGE SPECIFICATIONS**

Package	Reel Size	Reel DIA. (mm)	Q'TY/Reel (pcs)	Box Size (mm)	QTY/Box (pcs)	Carton Size (mm)	Q'TY/Carton (pcs)
SOT-23	7'	178	3000	203×203×195	45000	438×438×220	180000

### Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	$V_{GS}$	±20	]
Continuous Drain Current	l <sub>D</sub>	3	Α
Pulsed Drain Current 1)	I <sub>DM</sub>	10	Α
Maximum Power Dissipation 1),2)	P <sub>D</sub>	0.35	W
Tæ¢ā[ ~{ Junction V^{ ] ^ læč l^ Á	TJ	150	°C
Ù([ æ*^Á/^{ ] ^ æĕ  ^Á	T <sub>stg</sub>	-55 to 150	°C
Thermal Resistance from Junction-to-Ambient (t≤5s)	R <sub>θJA</sub>	357	°C/W

The above data are for reference only.

Notes
1) Pulse width limited by maximum junction temperature.

<sup>2)</sup> Surface Mounted on FR4 Board,  $t \le 5$  sec.



## MOSFET ELECTRICAL CHARACTERISTICS

# T<sub>a</sub>=25 °C unless otherwise specified

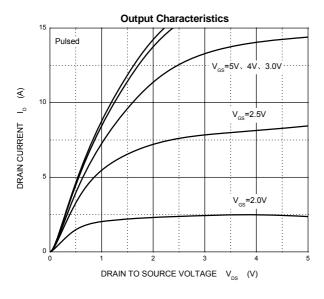
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V (BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V
Zero gate voltage drain current	IDSS	V <sub>DS</sub> =60V,V <sub>GS</sub> = 0V			1	μΑ
Gate-body leakage current	Igss	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage (note 3)	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5		2	V
Drain acurae en registence (note 2)	D	V <sub>GS</sub> =10V, I <sub>D</sub> =3A			105	Ω
Drain-source on-resistance (note 3)	RDS(on)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A			125	Ω
Forward tranconductance (note 3)	<b>g</b> FS	V <sub>DS</sub> =15V, I <sub>D</sub> =2A	1.4			S
Diode forward voltage (note 3)	V <sub>SD</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> = 0V			1.2	V
DYNAMIC CHARACTERISTICS (no	te 4)			•	•	
Input Capacitance	C <sub>iss</sub>			247		pF
Output Capacitance	Coss	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V,f =1MHz		34		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			19.5		pF
SWITCHING CHARACTERISTICS (I	note 4)			•	•	
Turn-on delay time	td(on)			6		ns
Turn-on rise time	tr	V <sub>GS</sub> =10V,V <sub>DD</sub> =30V,		15		ns
Turn-off delay time	<b>t</b> d(off)	I <sub>D</sub> =1.5A,R <sub>GEN</sub> =1Ω		15		ns
Turn-off fall time	tf			10		ns
Total Gate Charge	$Q_g$			6		nC
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =30V,V <sub>GS</sub> =4.5V,I <sub>D</sub> =3A		1		nC
Gate-Drain Charge	$Q_{gd}$			1.3		nC

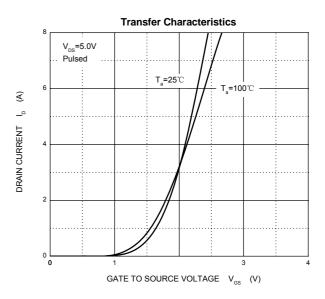
#### Notes:

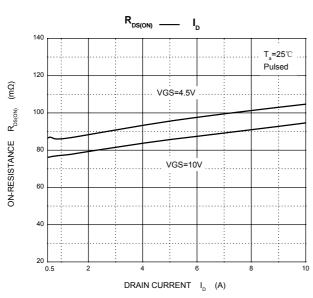
- 1. Repetitive rating : Pulse width limited by junction temperature.
- 2. Surface mounted on FR4 board , t≤10s.
- 3. Pulse Test : Pulse Width≤300µs, Duty Cycle≤0.5%.
- 4. Guaranteed by design, not subject to producting.

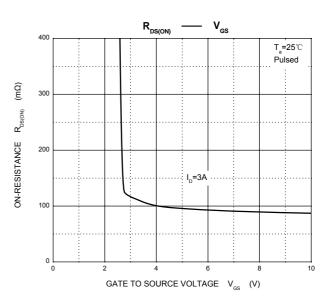


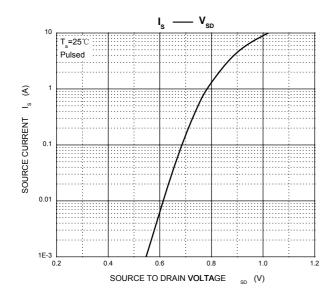
## **Typical Characteristics**

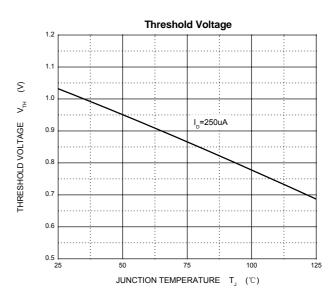








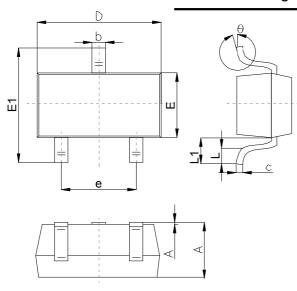






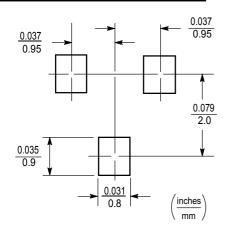
# **Outlitne Drawing**

## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters			
Symbol	Min	Тур	Max	
Α	1.00		1.40	
A1			0.10	
b	0.35		0.50	
С	0.10		0.20	
D	2.70	2.90	3.10	
Е	1.40		1.60	
E1	2.4		2.80	
е		1.90		
L	0.10		0.30	
L1	0.4			
θ	0°		10°	

## **Suggested Pad Layout**



#### Note:

Controlling

dimension:in/millimeters. 2.General

tolerance: ±0.05mm.

3. The pad layout is for reference purposes only.

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